




HIGH SENSITIVITY DRY-DEVELOPABLE PHOTORESIST FOR DEEP UV

Patent number: JP3152544
Publication date: 1991-06-28
Inventor: BRUNSVOLD WILLIAM R; CHIU PHILIP; CONLEY JR
WILLARD E; CROCKATT DALE M; MONTGOMERY
MELVIN W; MOREAU WAYNE MARTIN
Applicant: INTERNATL BUSINESS MACH CORP <IBM>
Classification:
- international: G03F7/039; C08G8/10; H01L21/027
- european:
Application number: JP19900250422 19900921
Priority number(s):

Also published as:

 EP0425411 (A2)
 US5023164 (A1)
 EP0425411 (A3)

Report a data error here

Abstract of JP3152544

PURPOSE: To enable dry development by using a phenol-aldehyde type condensation product and a photoactive compd. generating a strong acid which enables the reaction of hydroxy groups with an organometallic reagent when the compd. is exposed with deep UV.

CONSTITUTION: A phenol-aldehyde type condensation product represented by formula I and a radiation-degradable acid generating material such as a metallic or nonmetallic onium salt, a tosylate or a non-metal sulfonic acid precursor as a radiation sensitive material are used. In the formula I, R is H, -CH₃ or phenyl, R' is H, alkyl or aryl, R'' is H, halogen, nitro, alkoxy, alkyl, aryl or hydroxy and the basic arom. ring may be condensed with other cyclic structure so as to form a naphthol or anthracene unit. By such constitution, dry development is enabled.

Data supplied from the **esp@cenet** database - Patent Abstracts of Japan